

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A fabrication method of a liquid crystal display device, comprising:

forming a gate line on a substrate by applying a gate photoresist pattern by printing;

sequentially forming a gate insulating layer, a semiconductor layer, and a high-concentrated N+ layer over the gate line;

forming an active region ~~ever-including~~ the high-concentrated N+ layer by applying an active photoresist pattern by printing;

forming a conductive layer over the active region;

depositing a photoresist layer over the conductive layer;

applying a mask ~~ever-in~~ the photoresist layer, performing a lithography process, and thereby forming a source/drain electrode;

forming a passivation layer over the source/drain electrode;

forming a contact hole over the passivation layer by applying a contact hole photoresist pattern by printing; and

forming a pixel electrode on the passivation layer by printing a pixel electrode photoresist pattern.

2. (Original) The method of claim 1, wherein the mask includes a channel region pattern.

3. (Previously Presented) The method of claim 1, wherein the printing is roller printing.

4. (Original) The method of claim 1, wherein the step for forming the source/drain electrode comprises:

defining an active layer by sequentially removing the high-concentrated N+ layer and the semiconductor layer by using the active resist pattern formed by printing as a mask;

removing the active resist pattern;

sequentially forming a conductive layer and a photoresist layer over the active layer;

exposing the photoresist layer, performing a development process, and thereby removing the photoresist layer above a channel region by using the mask including the channel region pattern; and

sequentially removing the conductive layer and the high-concentrated N+ layer above the channel region.

5-14. (Cancelled)

15. (Previously Presented) The method of claim 1, wherein the mask applied over the photoresist layer in the step of applying the mask is the only mask applied through out the method of claim 1.

16. (Previously Presented) The method of claim 1, wherein the printing is ink jet printing.

17 - 19. (Canceled)

20. (Currently Amended) ~~The method of claim 17, wherein the step of forming the source and drain electrodes include:~~ A method for forming a liquid crystal display device, comprising:

forming a gate line on a substrate;

forming a gate insulating layer, a semiconductor layer, and an impurity-doped layer over the gate line;

forming an active region including the impurity-doped layer;

forming a conductive layer over the active region;

depositing a photoresist layer over the conductive layer;

applying a mask over the photoresist layer, patterning the photoresist layer using the mask, and thereby forming the source and drain electrodes using the patterned photoresist layer.

mask;

patterning the conductive layer using the patterned photoresist layer to form a source electrode and a drain electrode over the active region;

forming a passivation layer over the source and drain electrodes;

forming a contact hole in the passivation layer by applying a contact hole photoresist pattern by printing; and

forming a pixel electrode on the passivation layer by printing a pixel electrode photoresist pattern.

21. (Currently Amended) The method of claim 20, wherein the mask applied over the photoresist layer in the step of applying the mask is the only mask applied through out the method of ~~claim 17~~ claim 20.

22. (New) The method of claim 20, wherein the step of forming the gate line includes applying a gate photoresist pattern on the substrate by printing.

23. (New) The method of claim 20, wherein the step of forming the active region includes applying an active photoresist pattern including the impurity-doped layer by printing.